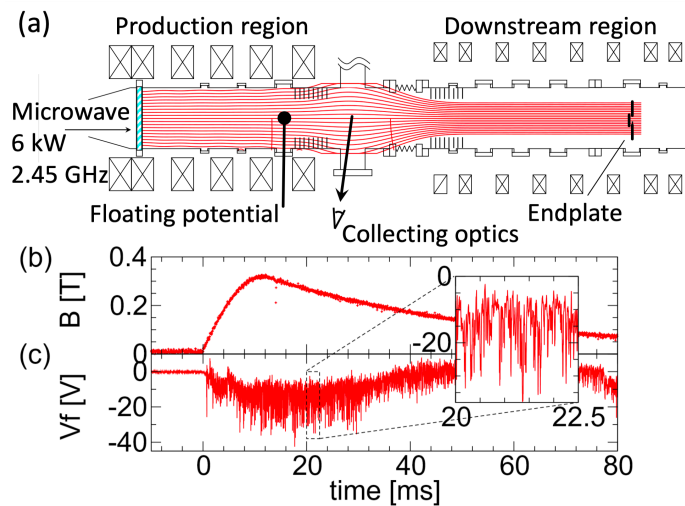


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The ion temperature during the intermittent negative spikes in floating potential is extracted using the conditional averaging method. For the first time, we have successfully observed a decrease in ion temperature during the intermittent events. (a) Schematic view of experimental setup in NUMBER. Typical temporal evolution of (b) magnetic field in the downstream region and (c) floating potential measured in the production region; an enlarged panel is also inserted.

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